

SANYO	No.3814	2SJ229
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Its height onboard is 9.5mm.
- Meets radial taping.

Absolute Maximum Ratings at Ta = 25°C

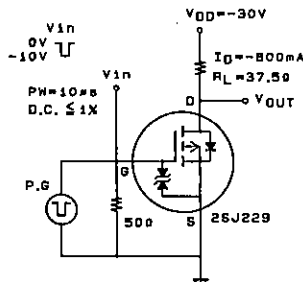
Drain to Source Voltage	V_{DS}	-60	V	unit
Gate to Source Voltage	V_{GS}	±15	V	
Drain Current(DC)	I_D	-1.6	A	
Drain Current(Pulse)	I_{DP}	-6.4	A	
Allowable Power Dissipation	P_D	1.5	W	
Channel Temperature	T_{ch}	150	°C	
Storage Temperature	T_{stg}	-55 to +150	°C	

$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$

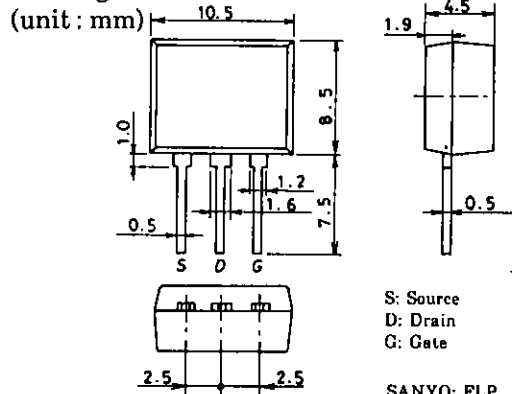
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -800mA$	1.0	1.8		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -800mA, V_{GS} = -10V$	0.35	0.45		Ω
	$R_{DS(on)}$	$I_D = -800mA, V_{GS} = -4V$	0.45	0.6		Ω
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		380		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		150		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		40		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12		ns
Rise Time	t_r	∕		18		ns
Turn-OFF Delay Time	$t_{d(off)}$	∕		90		ns
Fall Time	t_f	∕		55		ns
Diode Forward Voltage	V_{SD}	$I_S = -1.6A, V_{GS} = 0$	-1.0	-1.5		V

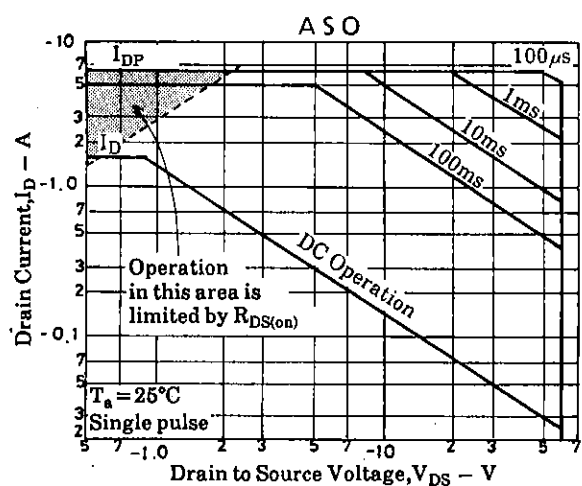
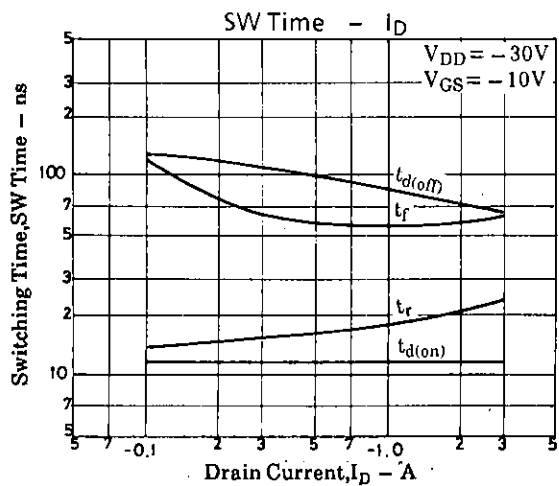
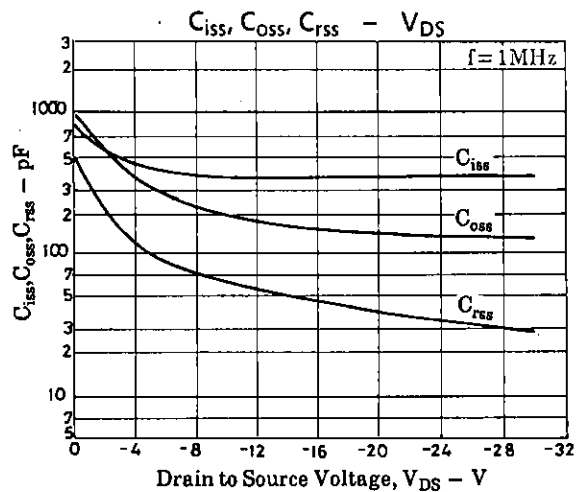
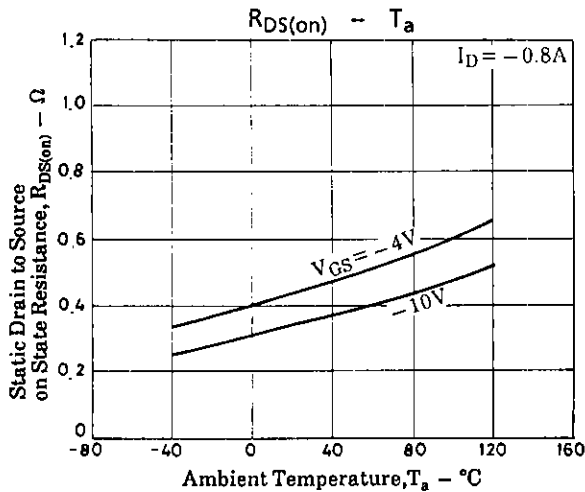
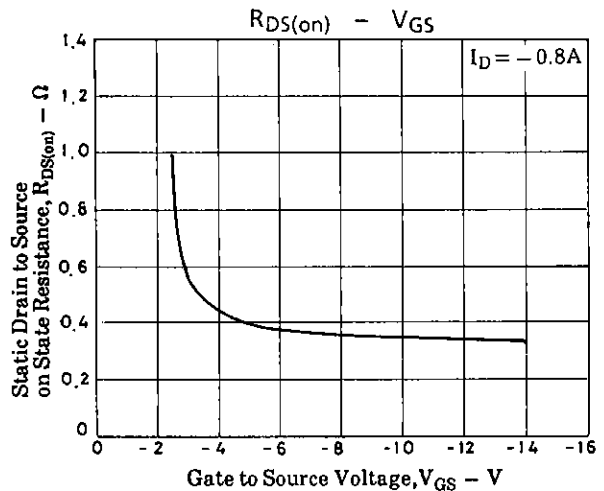
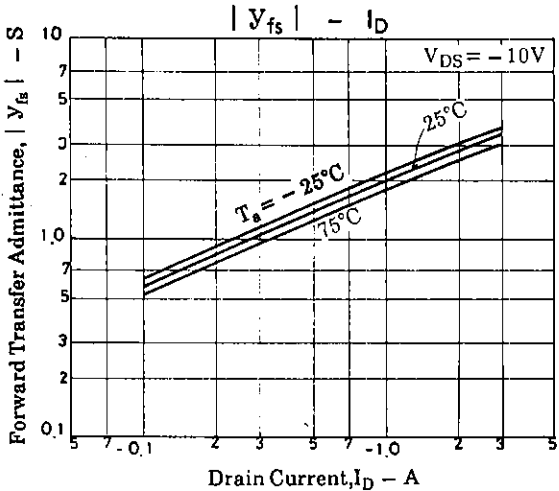
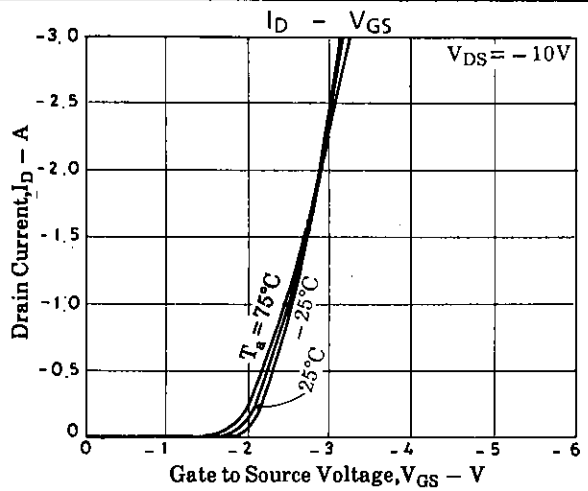
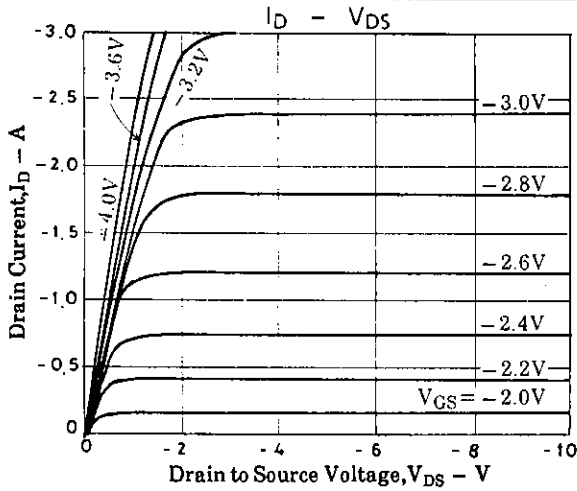
Switching Time Test Circuit

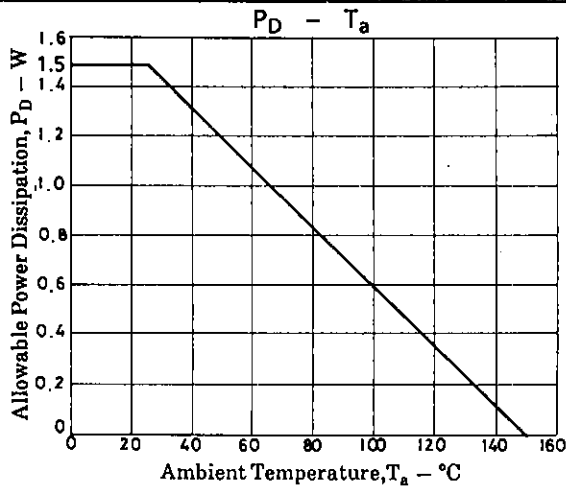


Package Dimensions 2085



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